REMARKS

In response to the Office Action dated April 28, 2005, applicant respectfully requests reconsideration.

As a preliminary matter, Applicant acknowledges, with appreciation, the indication of allowable subject matter in claims 1-8.

The spelling of "crystallographic" has been corrected in the claims. This change is grammatical only and does not narrow the scope of the claims.

The Office Action rejected claims 1, 4, and 5 under 35 U.S.C. §112, as not providing sufficient antecedent basis in specific instances. Corrections to overcome these rejections were suggested for claims 1 and 5. These corrections have been incorporated into the claims.

The Office Action indicated that there was insufficient antecedent basis for the limitation "germanium alloy". Applicant respectfully disagrees. The limitation in question reads "a silicon and germanium alloy" meaning that the alloy comprises silicon and germanium. Therefore, Applicant believes that the claim is correct as it stands and requires no correction.

Applicant wishes to note that the changes to claims 1 and 5 are for clarification only and do not narrow the scope of the claims.

In view of the changes to claims 1 and 5, Applicant respectfully requests that the rejection under 35 U.S.C. §112 be withdrawn.

Since the rejection under 35 U.S.C. §112 has been overcome, claims 1-8 should now be in allowable condition.

Applicant has also added claims 11-18 further define Applicant's contribution to the art.

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Claim 11 recites a method for growing a single-crystal region of a III-V compound on a surface corresponding to a crystallographic plane of a single-crystal silicon substrate, comprising growing by epitaxy on the substrate a single-crystal germanium layer, etching in the germanium layer an opening, the bottom of the opening corresponding to a single surface inclined with respect to said crystallographic plane or to several surfaces inclined with respect to said crystallographic plane; and growing the single-crystal III-V compound on the bottom of the opening. The cited art does not teach or suggest the limitations of claim 11.

Claims 12-18 depend from claim 11 and are allowable for at least the same reasons.

In view of the above amendment, applicant believes the pending application is in condition for allowance.

A Notice of Allowance is respectfully requested. The Examiner is requested to call the undersigned at the telephone number listed below if this communication does not place the case in condition for allowance.

If this response is not considered timely filed and if a request for an extension of time is otherwise absent, Applicant hereby requests any necessary extension of time. If there is a fee occasioned by this response, including an extension fee, that is not covered by an enclosed check, please charge any deficiency to Deposit Account No. 23/2825.

Dated: August 26, 2005

Respectfully submitted,

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